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EXAMINER

Serial No: 09/773,798

Docket: BUR920000143US1 (13890)

APPENDIX

10. The claims on appeal for U.S. Application Serial No. 09/773,798 filed February 1, 2001.

1. A method of fabricating a SiGe heterojunction bipolar transistor comprising the steps of:

providing a heterojunction bipolar transistor structure comprising at least an underlying SiGe base region, an insulator layer formed on surface portions of said underlying SiGe base region, and an emitter formed on said insulator layer and in contact with said underlying SiGe base region through an emitter opening formed in said insulator layer, said emitter, said insulator layer and said SiGe base region each having exposed sidewalls;

forming a permanent passivation layer on said exposed sidewalls of said emitter, said insulator layer and portions of said SiGe base region; and

siliciding exposed silicon surfaces of at least said emitter and said SiGe base region not protected by said permanent passivation layer to form silicide regions therein, wherein said permanent passivation layer prevents bridging between silicide regions thereby substantially eliminating shorts and improving bipolar yield by as much as 20-30%.